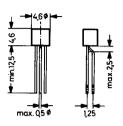
BF450, BF451

PNP Silicon Epitaxial Planar Transistors disigned for emitter-grounded AM and FM IF amplifier stages in which the negative pole of the supply voltage is grounded.

The BF 450 is designed for stages with AGC, and the BF 451 is designed for stages without AGC.





Plastic case \approx JEDEC TO 92 TO-18 compatible. The case is impervious to light.

Weight approximately 0.18 g Dimensions in mm

Absolute Maximum Ratings

	Symbol	Value	Unit	
Collector Base Voltage	-V _{CBO}	40	V	
Collector Emitter Voltage	-V _{CEO}	40	V	
Emitter Base Voltage	V _{EBO}	4	V	
Collector Current	-I _C	25	mA	
Base Current	−l _B	5	mA	
Power Dissipation at T _{amb} <45 °C	P _{tot}	250 ¹⁾	mW	
Junction Temperature	T _j	150	°C	
Storage Temperature Range	T _S	-55+150	°C	

Characteristics at $T_{amb} = 25\,^{\circ}\text{C}$

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at $-V_{CE} = 10 \text{ V}$, $-I_{C} = 1 \text{ mA}$ BF450 BF451	h _{FE}	60 30	_ _	<u>-</u> -	
Collector Base Breakdown Voltage at $-I_C = 10 \mu A$	-V _{(BR)CBO}	40	_	_	V
Collector Emitter Breakdown Voltage at -I _C = 2 mA	-V _{(BR)CEO}	40	_	_	V
Thermal Resistance Junction to Ambient	R _{thA}	****	_	420 ¹⁾	K/W
Collector Cutoff Current at -V _{CB} = 30 V	-I _{CBO}	_	_	50	nA
Gain Bandwidth Product at $-V_{CE} = 10 \text{ V}$, $-I_{C} = 1 \text{ mA}$, $f = 100 \text{ MHz}$	f _T	_	325	_	MHz
Feedback Capacitance at $-V_{CE} = 10 \text{ V}$, $-I_{C} = 1 \text{ mA}$, $f = 1 \text{ MHz}$	-C _{re}	_	0.35	_	pF
Real Part of Output Admittance at –V _{CE} = 10 V, –I _C = 1 mA, f = 0.5 MHz	g _{oe}	±is.		8	μS
Noise Figure at $-V_{CE} = 10 \text{ V}$, $-I_{C} = 1 \text{ mA}$, $f = 100 \text{ kHz}$, $R_{G} = 300 \Omega$	F	_	2	_	dB

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

